

NDF06N60Z

N-Channel Power MOSFET 600 V, 1.2 Ω

Features

- Low ON Resistance
- Low Gate Charge
- ESD Diode–Protected Gate
- 100% Avalanche Tested
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain–to–Source Voltage	V_{DSS}	600	V
Continuous Drain Current, $R_{\theta JC}$ (Note 1)	I_D	7.1	A
Continuous Drain Current $T_A = 100^\circ\text{C}$, $R_{\theta JC}$ (Note 1)	I_D	4.5	A
Pulsed Drain Current, $V_{GS} @ 10\text{ V}$	I_{DM}	28	A
Power Dissipation, $R_{\theta JC}$	P_D	35	W
Gate–to–Source Voltage	V_{GS}	± 30	V
Single Pulse Avalanche Energy, $L = 6.3\text{ mH}$, $I_D = 6.0\text{ A}$	E_{AS}	113	mJ
ESD (HBM) (JESD22–A114)	V_{esd}	3000	V
RMS Isolation Voltage ($t = 0.3\text{ sec.}$, $R.H. \leq 30\%$, $T_A = 25^\circ\text{C}$) (Figure 13)	V_{ISO}	4500	V
Peak Diode Recovery (Note 2)	dv/dt	4.5	V/ns
MOSFET dV/dt	dV/dt	60	V/ns
Continuous Source Current (Body Diode)	I_S	6.0	A
Maximum Temperature for Soldering Leads	T_L	260	$^\circ\text{C}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	–55 to 150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

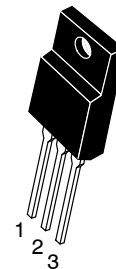
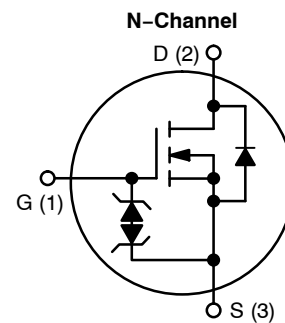
1. Limited by maximum junction temperature
2. $I_{SD} = 6.0\text{ A}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, $T_J = +150^\circ\text{C}$



ON Semiconductor®

www.onsemi.com

V_{DSS} (@ T_{Jmax})	$R_{DS(ON)}$ (MAX) @ 3 A
650 V	1.2 Ω



NDF06N60ZG,
NDF06N60ZH
TO–220FP
CASE 221AH

ORDERING AND MARKING INFORMATION

See detailed ordering, marking and shipping information on page 6 of this data sheet.

NDF06N60Z

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	3.6	°C/W
Junction-to-Ambient Steady State (Note 3)	$R_{\theta JA}$	50	

3. Insertion mounted

Electrical Characteristics (T_J = 25°C unless otherwise noted)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	BV_{DSS}	600			V
Breakdown Voltage Temperature Co-efficient	Reference to 25°C, $I_D = 1\text{ mA}$	$\Delta BV_{DSS}/\Delta T_J$		0.6		V/°C
Drain-to-Source Leakage Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	25°C			1	μA
		150°C			50	
Gate-to-Source Forward Leakage	$V_{GS} = \pm 20\text{ V}$	I_{GSS}			±10	μA

ON CHARACTERISTICS (Note 4)

Static Drain-to-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 3.0\text{ A}$	$R_{DS(on)}$		0.98	1.2	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 100\text{ μA}$	$V_{GS(th)}$	3.0	3.9	4.5	V
Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 3.0\text{ A}$	g_{FS}		5.0		S

DYNAMIC CHARACTERISTICS

Input Capacitance (Note 5)	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	C_{iss}	738	923	1107	pF
Output Capacitance (Note 5)		C_{oss}	90	106	125	
Reverse Transfer Capacitance (Note 5)		C_{rss}	15	23	30	
Total Gate Charge (Note 5)	$V_{DD} = 300\text{ V}, I_D = 6.0\text{ A},$ $V_{GS} = 10\text{ V}$	Q_g	15.5	31	47	nC
Gate-to-Source Charge (Note 5)		Q_{gs}	3	6.3	9.5	
Gate-to-Drain ("Miller") Charge (Note 5)		Q_{gd}	8	17	24.5	
Plateau Voltage		V_{GP}		6.4		V
Gate Resistance		R_g		3.2		Ω

RESISTIVE SWITCHING CHARACTERISTICS

Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 6.0\text{ A},$ $V_{GS} = 10\text{ V}, R_G = 5\text{ Ω}$	$t_{d(on)}$		13		ns
Rise Time		t_r		17		
Turn-Off Delay Time		$t_{d(off)}$		30		
Fall Time		t_f		28		

SOURCE-DRAIN DIODE CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Diode Forward Voltage	$I_S = 6.0\text{ A}, V_{GS} = 0\text{ V}$	V_{SD}			1.6	V
Reverse Recovery Time	$V_{GS} = 0\text{ V}, V_{DD} = 30\text{ V}$ $I_S = 6.0\text{ A}, di/dt = 100\text{ A/μs}$	t_{rr}		338		ns
Reverse Recovery Charge		Q_{rr}		2.0		μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.

5. Guaranteed by design.

TYPICAL CHARACTERISTICS

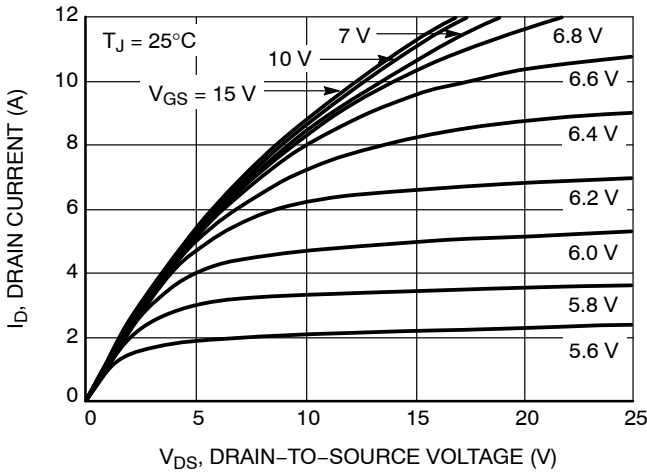


Figure 1. On-Region Characteristics

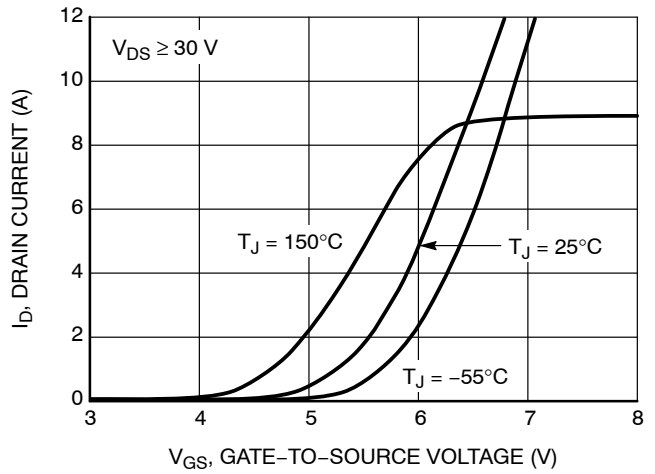


Figure 2. Transfer Characteristics

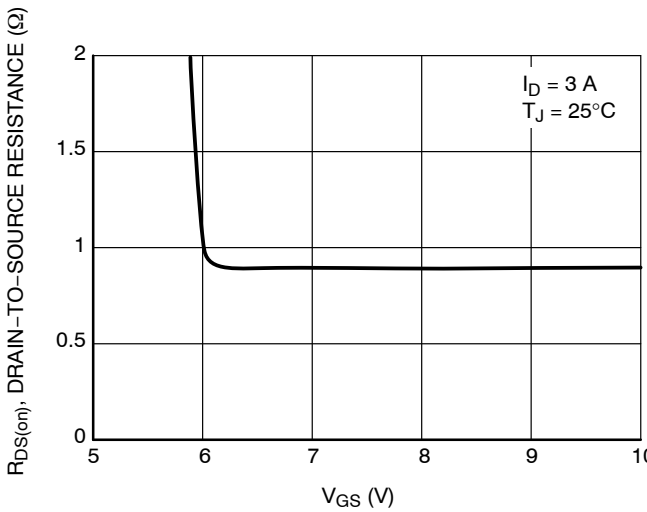


Figure 3. On-Resistance vs. V_{GS}

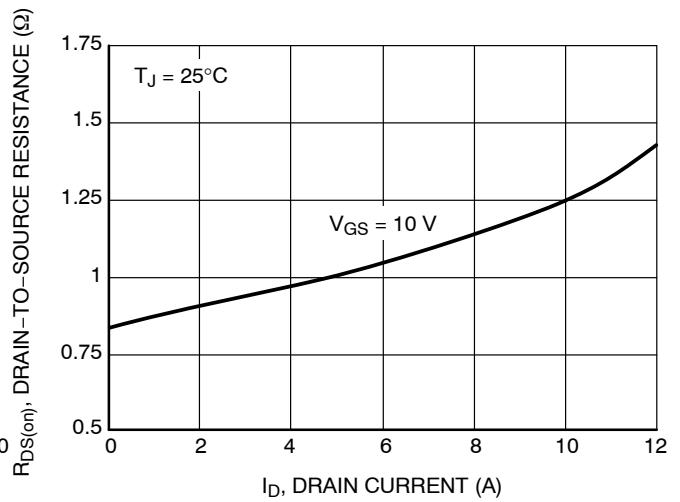


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

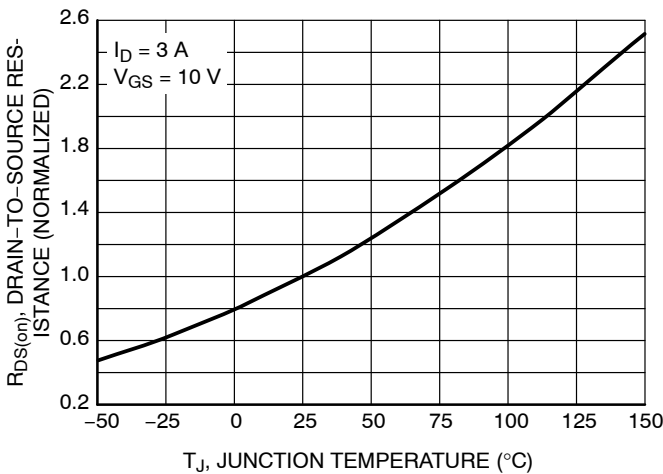


Figure 5. On-Resistance Variation with Temperature

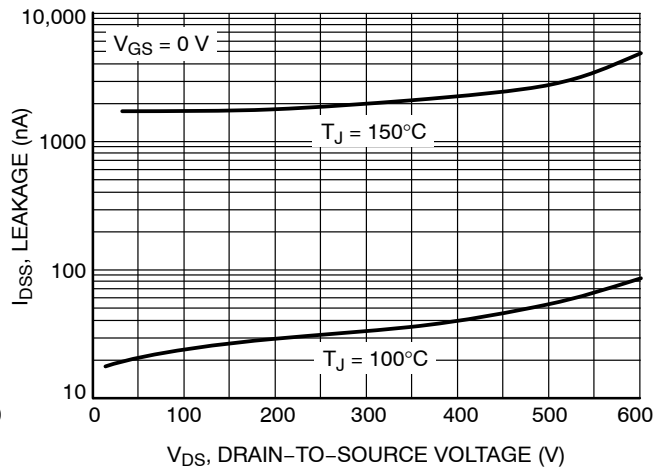


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NDF06N60Z

TYPICAL CHARACTERISTICS

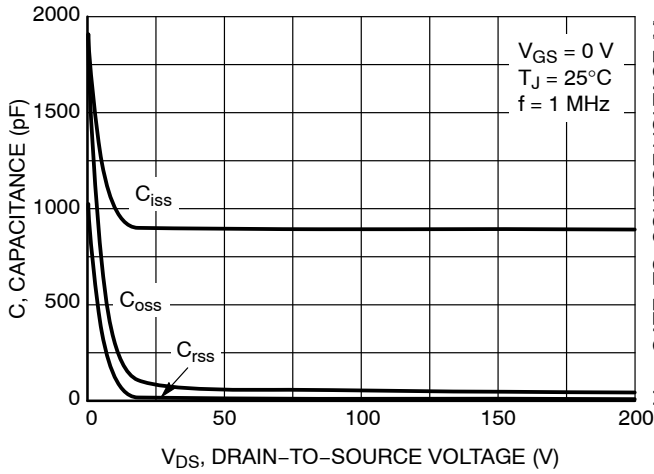


Figure 7. Capacitance Variation

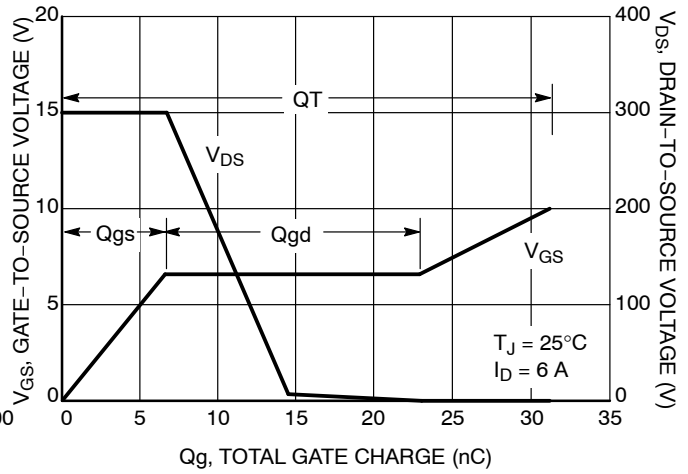


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

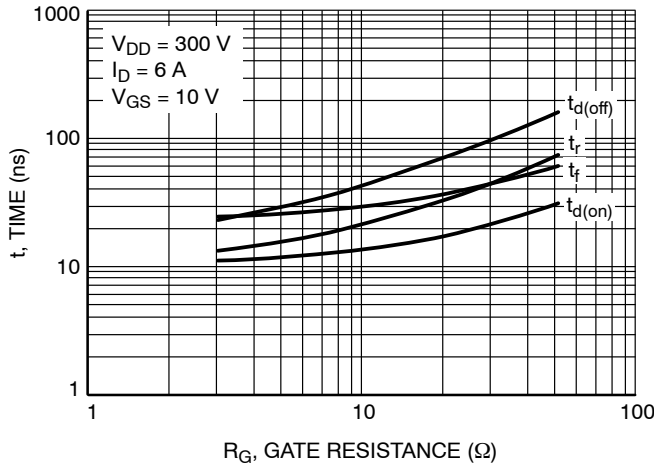


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

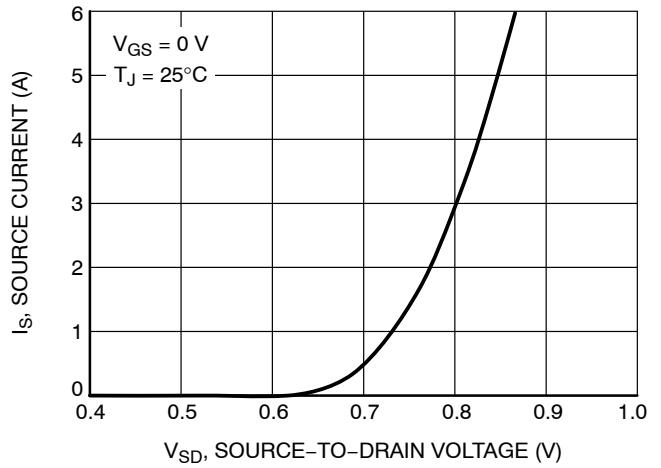


Figure 10. Diode Forward Voltage vs. Current

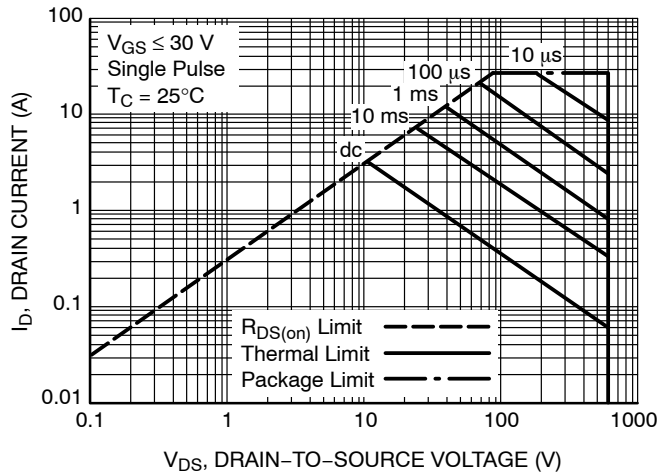


Figure 11. Maximum Rated Forward Biased Safe Operating Area for NDF06N60Z

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TYPICAL CHARACTERISTICS

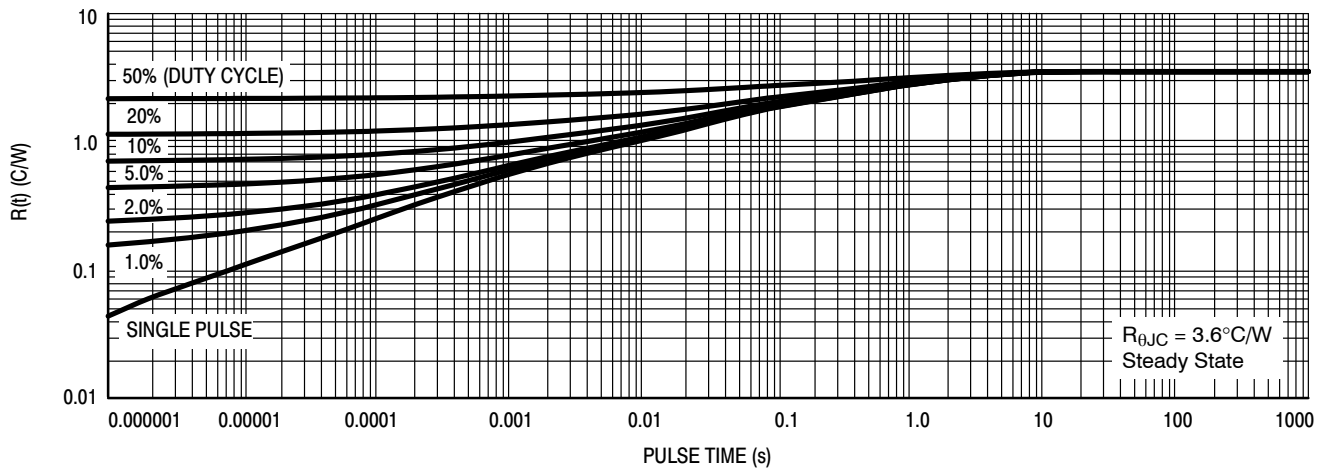


Figure 12. Thermal Impedance for NDF06N60Z

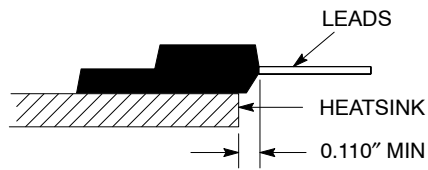


Figure 13. Mounting Position for Isolation Test

Measurement made between leads and heatsink with all leads shorted together.

*For additional mounting information, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

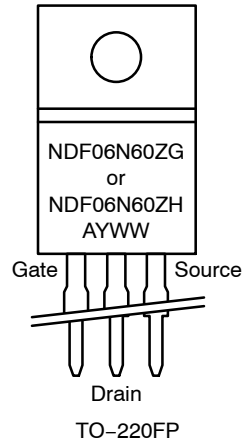
NDF06N60Z

ORDERING INFORMATION

Order Number	Package	Shipping†
NDF06N60ZG	TO-220FP (Pb-Free, Halogen-Free)	50 Units / Rail
NDF06N60ZH	TO-220FP (Pb-Free, Halogen-Free)	50 Units / Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MARKING DIAGRAMS

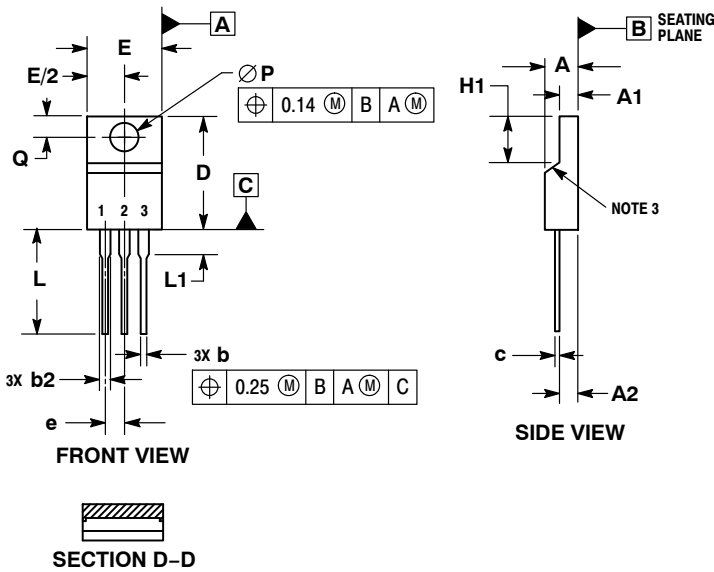


A = Location Code
Y = Year
WW = Work Week
G, H = Pb-Free, Halogen-Free Package

NDF06N60Z

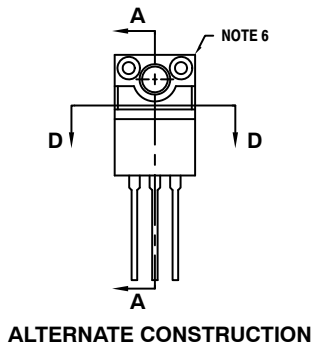
PACKAGE DIMENSIONS


TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE F



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOPE DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.



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